Physics ICS Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	When a PN-Junction is reverse biased the depletion region is.	A. Widened B. Narrowed C. Normal D. None of these
2	Reverse current flows due to	A. Majority charge carriers B. Minority charge carriers C. Electrons D. Holes
3	The potential difference across the depletion region of germanium is.	A. 0.3 V B. 0.5 V C. 0.7 V D. 0.8 V
4	The potential barrier for silicon is.	A. 0.7 V B. 0.5 V C. 0.3 V D. 0.9 V
5	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
6	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
7	Most of the electrons in the base of an NPN transistor flow:	A. Out of the base lead B. Into the collector C. Into the emit D. Into the base supply
8	When transistor are used in digital circuits they usually operate in the :	A. Active region B. Break down region C. Saturation & cutoff regions D. Linear region
9	Improper bisting of a transistor circiut produces:	A. Heavy loading of emitter current B. Distortion in the output output signal C. Excessive heat at collector terminal D. Faculty location of load line
10	The reverse saturation current in a PN junction diode is only due to:	A. Majority carriers B. Minoritycarriers C. Acceptor ions D. Donor ions
11	In an N-type silicon, which of the following statement is true?	A. Electrons are majority carriers & trivalent atoms are the dopants B. Electrons are majority carriers & pentavalent atoms are the dopants C. Holes are minority carriers & pentavalent atoms are the dopants. D. Holes are minority carriers & trivavalent atoms are the dopants.
12	Which device is used as a rectifier?	A. Capacitor B. Transistor C. Diode D. Transformer
13	A transistor has parts:	A. 2 B. 3 C. 4 D. 5
14	Conversion of A.C into D.C is called:	A. Compton effect B. Rectification

		C. Amplification D. Pair production
15	OR gate is represented by:	A. X = A+B B. X=A.B C. X=A+B D. X=A.B
16	NAND gate represented by:	A. X = A. B B. X = A+B C. X= A.B D. X=|A+B|
17	For normal use:	A. Emitter base function is reversed biased B. Collector base junction is reserved biased C. Emitter base junction is forward biased D. Both c and b